



BSC119N03S G Information



For Reference Only

Part Number BSC119N03S G **Manufacturer** Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 30V 30A TDSON-8

Package 8-PowerTDFN

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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BSC119N03S G Specifications

Manufacturer Part NumberBSC119N03S GManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor Products Transistors - FETs, MOSFETs - SinglePackage8-PowerTDFNSeriesOptiMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C11.9A (Ta), 30A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 20µAGate Charge (Qg) (Max) @ Vgs11nC @ 5VInput Capacitance (Ciss) (Max) @ Vds1370pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.8W (Ta), 43W (Tc)Rds On (Max) @ Id, Vgs11.9 mOhm @ 30A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TDSON-8Package / Case8-PowerTDFN		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single 8-PowerTDFN Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Train to Source Voltage (Vdss) Ourrent - Continuous Drain (Id) @ 25°C 11.9A (Ta), 30A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1370pF @ 15V Vgs (Max) ### 20V ###	Manufacturer Part Number	BSC119N03S G
Package 8-PowerTDFN Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 11.9A (Ta), 30A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 20μA Gate Charge (Qg) (Max) @ Vgs 11nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 1370pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.8W (Ta), 43W (Tc) Rds On (Max) @ Id, Vgs 11.9 mOhm @ 30A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TDSON-8 Package / Case 8-PowerTDFN	Manufacturer	Infineon Technologies
Package 8-PowerTDFN Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 11.9A (Ta), 30A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 20µA Gate Charge (Qg) (Max) @ Vgs 11nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 1370pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.8W (Ta), 43W (Tc) Rds On (Max) @ Id, Vgs 11.9 mOhm @ 30A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TDSON-8 Package / Case 8-PowerTDFN	Category	Discrete Semiconductor Products
Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 11.9A (Ta), 30A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 20µA Gate Charge (Qg) (Max) @ Vgs 11nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 1370pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.8W (Ta), 43W (Tc) Rds On (Max) @ Id, Vgs 11.9 mOhm @ 30A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TDSON-8 Package / Case 8-PowerTDFN		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) 30V Current - Continuous Drain (Id) @ 25°C 11.9A (Ta), 30A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) **ET Feature** Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.9 mOhm @ 30A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case N-Channel MOSFET (Metal Oxide) MOSFET (Metal Oxide) 30V **Channel **MOSFET (Metal Oxide) 11.9A (Ta), 30A (Tc) 11.9A (Ta), 30A (Tc) 11.9C @ 5V 1	Package	8-PowerTDFN
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 11.9A (Ta), 30A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs 11nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 1370pF @ 15V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.9 mOhm @ 30A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TDSON-8 Package / Case MOSFET (Metal Oxide) 30V Rds OK (Max) (Retal Oxide) 11.9A (Ta), 30A (Tc) 11.9A (Ta), 30A (Tc	Series	OptiMOS?
Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C11.9A (Ta), 30A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 20μAGate Charge (Qg) (Max) @ Vgs11nC @ 5VInput Capacitance (Ciss) (Max) @ Vds1370pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.8W (Ta), 43W (Tc)Rds On (Max) @ Id, Vgs11.9 mOhm @ 30A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TDSON-8Package / Case8-PowerTDFN	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.9 mOhm @ 30A, 10V Operating Temperature Supplier Device Package Package / Case 11.9 M (Ta), 30A (Tc) 11.9 V 4.5V, 10V 4.5V, 10V 2.0µA 1370pF @ 15V 1370pF @ 15V 2.8W (Ta), 43W (Tc) 11.9 mOhm @ 30A, 10V -55°C ~ 150°C (TJ) Surface Mount PG-TDSON-8 8-PowerTDFN	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 20μAGate Charge (Qg) (Max) @ Vgs11nC @ 5VInput Capacitance (Ciss) (Max) @ Vds1370pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.8W (Ta), 43W (Tc)Rds On (Max) @ Id, Vgs11.9 mOhm @ 30A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TDSON-8Package / Case8-PowerTDFN	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.9 mOhm @ 30A, 10V Operating Temperature Supplier Device Package Package / Case 8-PowerTDFN	Current - Continuous Drain (Id) @ 25°C	11.9A (Ta), 30A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1370pF @ 15V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.9 mOhm @ 30A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-PowerTDFN	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) E20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.9 mOhm @ 30A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TDSON-8 Package / Case 8-PowerTDFN	Vgs(th) (Max) @ Id	2V @ 20μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)2.8W (Ta), 43W (Tc)Rds On (Max) @ Id, Vgs11.9 mOhm @ 30A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TDSON-8Package / Case8-PowerTDFN	Gate Charge (Qg) (Max) @ Vgs	11nC @ 5V
FET Feature - Power Dissipation (Max) 2.8W (Ta), 43W (Tc) Rds On (Max) @ Id, Vgs 11.9 mOhm @ 30A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TDSON-8 Package / Case 8-PowerTDFN	Input Capacitance (Ciss) (Max) @ Vds	1370pF @ 15V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.9 mOhm @ 30A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TDSON-8 Package / Case 8-PowerTDFN	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs11.9 mOhm @ 30A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TDSON-8Package / Case8-PowerTDFN	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TDSON-8 Package / Case 8-PowerTDFN	Power Dissipation (Max)	2.8W (Ta), 43W (Tc)
Mounting Type Surface Mount Supplier Device Package Package / Case Supplier Device Package PG-TDSON-8 8-PowerTDFN	Rds On (Max) @ Id, Vgs	11.9 mOhm @ 30A, 10V
Supplier Device Package PG-TDSON-8 Package / Case 8-PowerTDFN	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-PowerTDFN	Mounting Type	Surface Mount
	Supplier Device Package	PG-TDSON-8
Report errors?	Package / Case	8-PowerTDFN
		Report errors?

BSC119N03S G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

BSC119N03S G Payment Methods



















BSC119N03S G Shipping Methods













If you have any question about BSC119N03S G, please do not hesitate to contact us!

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